

DESCRIPTION

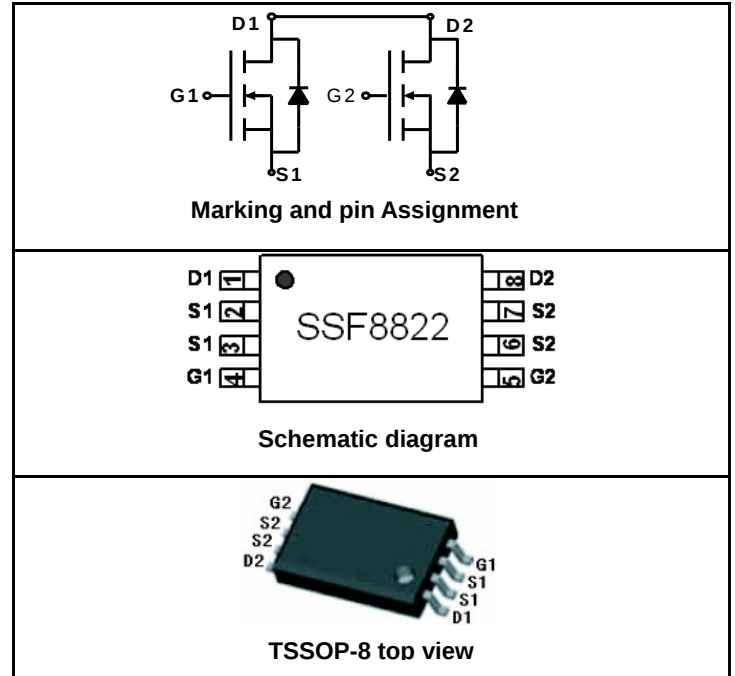
The SSF8822 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 0.8V. This device is suitable for use as a uni-directional or bi-directional load switch, facilitated by its common-drain configuration.

GENERAL FEATURES

- $V_{DS} = 20V, I_D = 7A$
 $R_{DS(ON)} < 21m\Omega @ V_{GS}=10V$
 $R_{DS(ON)} < 24m\Omega @ V_{GS}=4.5V$
 $R_{DS(ON)} < 28m\Omega @ V_{GS}=3.6V$
 $R_{DS(ON)} < 32m\Omega @ V_{GS}=2.5V$
 $R_{DS(ON)} < 50m\Omega @ V_{GS}=1.8V$
- High Power and current handling capability
- Lead free product is acquired
- Surface Mount Package

Application

- Battery protection
- Load switch
- Power management



PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
SSF8822	SSF8822	TSSOP-8	Ø330mm	12mm	3000 units

ABSOLUTE MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous@ Current-Pulsed (Note 1)	I_D	7	A
	I_{DM}	30	A
Maximum Power Dissipation	P_D	1.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	83	°C/W
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ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=16V, V_{GS}=0V$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$			±100	nA

ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =1mA	0.5	0.8	1	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =7A		16.4	21	mΩ
		V _{GS} =4.5V, I _D =6.6A		19	24	
		V _{GS} =3.6V, I _D =6A		21.7	28	
		V _{GS} =2.5V, I _D =5.5A		25	32	
		V _{GS} =1.8V, I _D =2A		36	50	
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =7A		24		S
DYNAMIC CHARACTERISTICS (Note4)						
Input Capacitance	C _{ISS}	V _{DS} =10V, V _{GS} =0V, F=1.0MHz		630		PF
Output Capacitance	C _{OSS}			160		PF
Reverse Transfer Capacitance	C _{rSS}			135		PF
SWITCHING CHARACTERISTICS (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DS} =10V, R _L =1.4Ω V _{GS} =5V, R _{GEN} =3Ω		5.7		nS
Turn-on Rise Time	t _r			11.5		nS
Turn-Off Delay Time	t _{d(off)}			31.5		nS
Turn-Off Fall Time	t _f			9.7		nS
Total Gate Charge	Q _g	V _{DS} =10V, I _D =7A, V _{GS} =4.5V		9.3		nC
Gate-Source Charge	Q _{gs}			0.6		nC
Gate-Drain Charge	Q _{gd}			3.6		nC
Body Diode Reverse Recovery Time	trr	IF=7A, dI/dt=100A/μs		15.2		nS
Body Diode Reverse Recovery Charge	Qrr	IF=7A, dI/dt=100A/μs		6.3		nC
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =1A		0.7	1	V
Diode Forward Current (Note 2)	I _S				2.5	A

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production testing.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

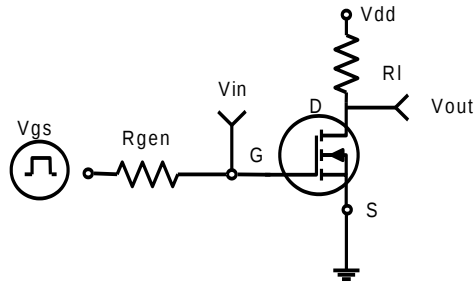


Figure 1: Switching Test Circuit

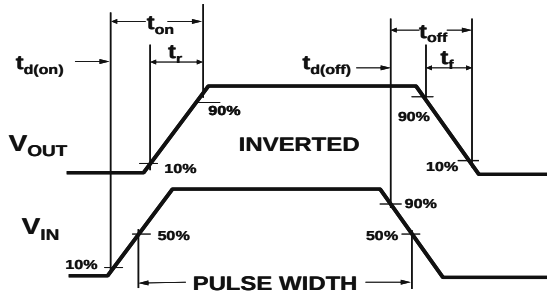


Figure 2: Switching Waveforms

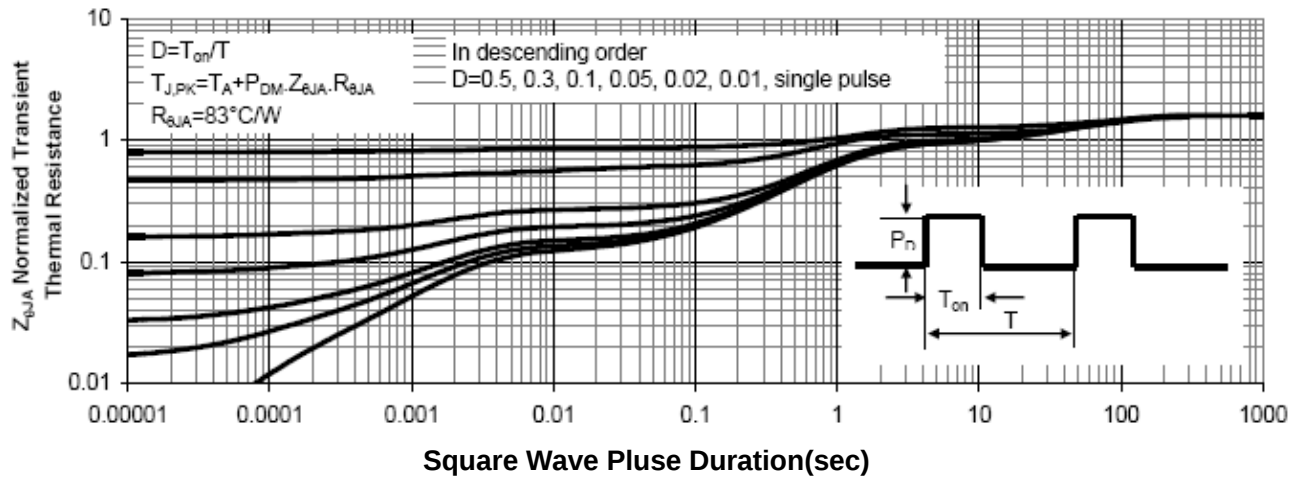
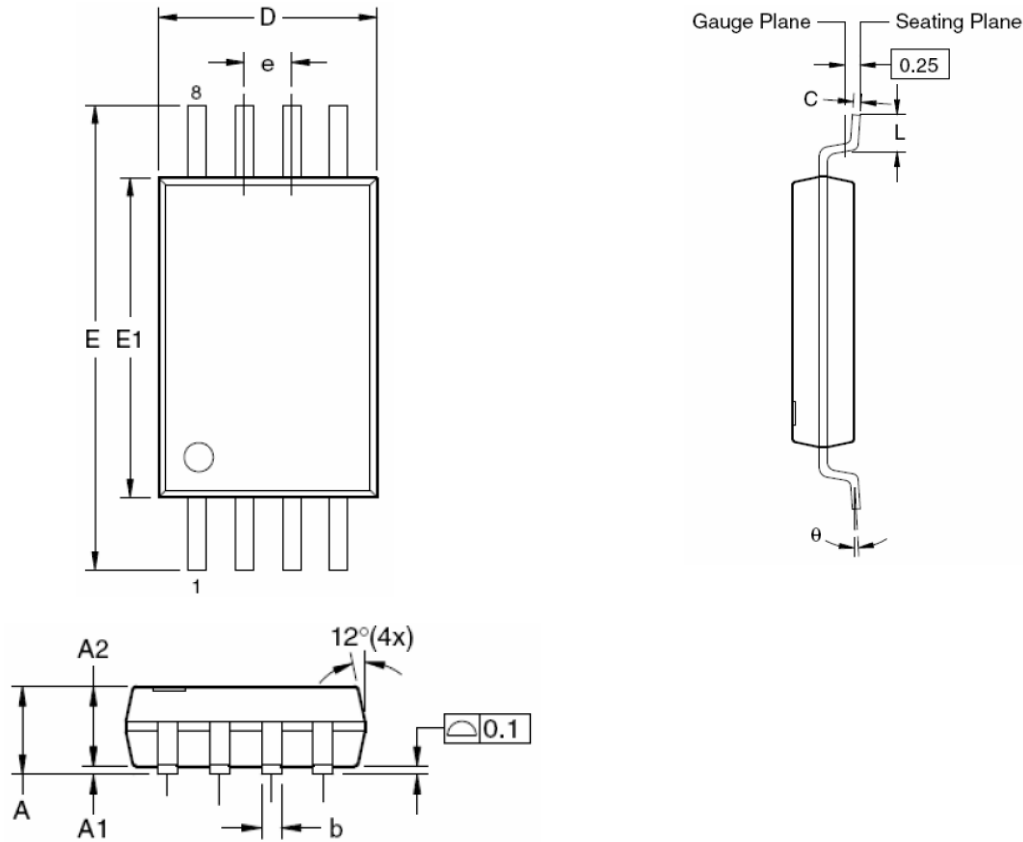
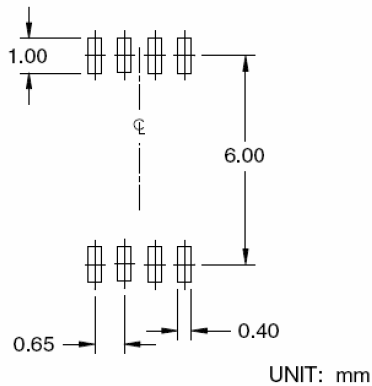


Figure 3: Normalized Maximum Transient Thermal Impedance

TSSOP-8 PACKAGE INFORMATION



RECOMMENDED LAND PATTERN



Dimensions in millimeters

Symbols	Min.	Nom.	Max.
A	—	—	1.20
A1	0.05	—	0.15
A2	0.80	1.00	1.05
b	0.19	—	0.30
C	0.09	—	0.20
D	2.90	3.00	3.10
E	6.40 BSC		
E1	4.30	4.40	4.50
e	0.65 BSC		
L	0.45	0.60	0.75
θ	0°	—	8°

Dimensions in inches

Symbols	Min.	Nom.	Max.
A	—	—	0.047
A1	0.002	—	0.006
A2	0.031	0.039	0.041
b	0.007	—	0.012
C	0.004	—	0.008
D	0.114	0.118	0.122
E	0.252 BSC		
E1	0.169	0.173	0.177
e	0.026 BSC		
L	0.018	0.024	0.030
θ	0°	—	8°

NOTES:

1. Dimensions are inclusive of plating
2. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 6 mils.
3. Dimension L is measured in gauge plane.
4. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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